

**IN THE CLAIMS**

1. (Currently Amended) A semiconductor laser light emitting device comprising:  
~~a stacked film composed of~~ a stack of group III nitride semiconductor films;  
wherein each containing at least one kind group III nitride semiconductor film  
comprises an element selected from the group consisting of aluminum, gallium, indium, and boron;  
  
wherein, an upper portion of said ~~stacked film~~ stack of group III nitride semiconductor films comprises ~~is formed into a ridge like stripe, to form~~ a current injection region;  
  
wherein a current injection width  $W_{st}$  of said current injection region is at a value in a range of  $1\ \mu\text{m} \leq W_{st} \leq 3\ \mu\text{m}$ [[,]]; and  
  
wherein said current injection region is formed on an active layer;  
  
a current non-injection region formed on both sides of said ~~ridge like strip~~ current injection region, wherein [[,]] ~~at least part of~~ said current non-injection region comprises ~~is made from~~ a material expressed by a chemical formula  $\text{Al}_x\text{Ga}_{1-x}\text{N}$  ( $0 \leq x \leq 1.0$ ); wherein the component ratio “x” of Al is at a value in a range of  $0.3 \leq x \leq 1.0$ ; ~~so that said semiconductor laser light emitting device is configured as an index guide type semiconductor laser light emitting device;~~ and  
  
wherein the group III nitride semiconductor films ~~a film~~ located between ~~an~~ the active layer and the current non-injection region ~~of the stacked film made from,~~ comprises a material expressed by a chemical formula  $\text{Al}_x\text{Ga}_{1-x}\text{N}$  ( $0.3 \leq x \leq 1.0$ ), and ~~has~~ have a combined thickness of less than or equal to  $0.2\ \mu\text{m}$  but greater than zero.

Claims 2-4 (Cancelled)

5. (Original) A semiconductor laser light emitting device according to claim 1, wherein a difference  $\Delta n$  between an effective refractive index  $n_1$  of said current injection region in the film stacking direction and an effective refractive index  $n_2$  of said current non-injection region in the film stacking direction is in a range of  $0.007 \leq \Delta n = (n_1 - n_2) \leq 0.012$ .

Claims 6-8 (Cancelled)

9. (Currently Amended) A semiconductor laser light emitting device comprising:  
~~a stacked film composed of~~ a stack of group III nitride semiconductor films;  
wherein each containing at least one kind group III nitride semiconductor film comprises  
an element selected from the group consisting of aluminum, gallium, indium, and boron;  
wherein, an upper portion of said ~~stacked film~~ stack of group III nitride semiconductor  
films comprises ~~is formed into a ridge-like stripe, to form~~ a current injection region;  
wherein a current injection width  $W_{st}$  of said current injection region is at a value in a  
range of  $1 \mu m \leq W_{st} \leq 3 \mu m$  ~~[[,]]; and~~  
wherein said current injection region is formed on an active layer;  
a current non-injection region formed on both sides of said ~~ridge-like strip~~ current  
injection region, wherein ~~[[,]] and at least part of~~ said current non-injection region comprises is

~~made from~~ a material expressed by a chemical formula  $\text{Al}_x\text{Ga}_{1-x}\text{N}$  ( $0 \leq x \leq 1.0$ ); wherein the

component ratio "x" of Al is at a value in a range of  $0.15 < x < 0.30$ [[,]]

~~so that said semiconductor laser light emitting device is configured as a weak index type~~

~~pulsation semiconductor laser light emitting device; and~~

wherein the group III nitride semiconductor films ~~a film~~ located between ~~an~~ the active layer and the current non-injection region ~~of the stacked film made from,~~ comprises a material expressed by a chemical formula  $\text{Al}_x\text{Ga}_{1-x}\text{N}$  ( $0.15 \leq x \leq 0.30$ ), and ~~has~~ have a combined thickness of less than or equal to  $0.2 \mu\text{m}$  but greater than zero.

Claims 10-12 (Cancelled)

13. (Original) A semiconductor laser light emitting device according to claim 9, wherein a difference  $\Delta n$  between an effective refractive index  $n_1$  of said current injection region in the film stacking direction and an effective refractive index  $n_2$  of said current non-injection region in the film stacking direction is in a range of  $0 < \Delta n = (n_1 - n_2) < 0.007$ .

Claims 14-24 (Cancelled)

25. (Currently Amended) A semiconductor laser light emitting device comprising:  
a stack of group III nitride semiconductor films each comprising at least one element selected from the group of aluminum, gallium, indium, and boron;

an upper portion of said ~~stacked film~~ stack of group III nitride semiconductor films  
comprises forming a ridge-like stripe for a current injection region;

wherein a current non-injection region formed on both sides of said ridge-like strip,  
wherein ~~at least part of~~ said current non-injection region comprises ~~is made from~~ a material  
expressed by a chemical formula  $\text{Al}_x\text{Ga}_{1-x}\text{N}$  ( $0 \leq x \leq 1.0$ ), and wherein the component ratio "x"  
of Al is between 0.3 and 1.0; and

a p-side electrode is formed on and in contact with the current non-injection region.

26. (Currently Amended) A semiconductor laser light emitting device comprising:  
a stack of group III nitride semiconductor films each comprising at least one element  
selected from the group of aluminum, gallium, indium, and boron;

an upper portion of said stacked film forming a ridge-like stripe for a current injection  
region;

a current non-injection region formed on both sides of said ridge-like strip, wherein at  
least part of said current non-injection region is made from a material expressed by a chemical  
formula  $\text{Al}_x\text{Ga}_{1-x}\text{N}$  ( $0 \leq x \leq 1.0$ ), and wherein the component ratio "x" of Al is between 0.3 and  
1.0; and

a contact layer formed ~~in-between~~ on the current injection region, wherein the current  
non-injection region is formed on both sides of said contact layer.

27. (Previously Presented) A semiconductor laser light emitting device  
according to claim 26, wherein the contact layer is formed on the ridge-like stripe.

28. (Previously Presented) A semiconductor laser light emitting device according to claim 27, wherein the contact layer is in contact with the ridge-like stripe.

29. (Previously Presented) A semiconductor laser light emitting device according to claim 26, further comprising a p-side electrode is formed on and in contact with the contact layer.

30. (Currently Amended) A semiconductor laser light emitting device comprising:  
a stack of group III nitride semiconductor films;

wherein each group III nitride semiconductor film comprises an element selected from the group consisting ~~comprising at least one element selected from the group~~ of aluminum, gallium, indium, and boron;

wherein, an upper portion of said ~~stacked film~~ stack of group III nitride semiconductor films comprises ~~forming a ridge-like stripe for~~ a current injection region;

wherein a current non-injection region formed on both sides of said ~~ridge-like strip~~ current injection region, wherein ~~at least part of~~ said current non-injection region comprises is ~~made from~~ a material expressed by a chemical formula  $\text{Al}_x\text{Ga}_{1-x}\text{N}$  ( $0 \leq x \leq 1.0$ ); and

wherein the group III nitride semiconductor films ~~a film~~ located between ~~an~~ the active layer and the current non-injection region ~~of the stacked film made from,~~ comprises a material expressed by a chemical formula  $\text{Al}_x\text{Ga}_{1-x}\text{N}$  ( $0.15 \leq x \leq 0.30$ ), and ~~having~~ have a combined thickness of less than or equal to  $0.2 \mu\text{m}$  but greater than zero.